

ICDS 2011 PROGRAMME

SATURDAY 16 th July 2011	MONDAY 18 th July 2011	TUESDAY 19 th July 2011		WEDNESDAY 20 th July 2011		THURSDAY 21 st July 2011		FRIDAY 22 nd July 2011		
TUTORIAL DAY	PLENARY SESSION	Defects in nano-structures	Defects in Ge 1	Defects in Ge 2	Defects in Organic semi-conductors	Defects in Compound semi-conductors	Defects in Oxides 3	Defects in Magnetic semi-conductors 1	Defects in Si 4	
		1020 – 1045 COFFEE BREAK								
		PV 1	Theory	Defects in nitrides 1	Defects in Oxides 1	Defects in Oxides 2	Defects in Si 2	Defects in Oxides 4	Defects in nitrides 2	Defects in Magnetic semi-conductors 2
SUNDAY 17 th July 2011	1230 - 1345 LUNCH							1150-1230 End of conference		
REGISTRATION 1700 onwards, Rutherford Hotel, Nelson	PV 2	Defects in SiC	Rare earths	Defects in Si 1	1230-1800 OPTIONAL LOCAL EXCURSIONS (varying length)	Defects in Si 3				
WELCOME FUNCTION From 1815	POSTER SESSION		POSTER SESSION			POSTER SESSION				
EVENING FREE FOR DINNER IN CITY	EVENING FREE FOR DINNER IN CITY (plus Committee Dinner)		EVENING FREE FOR DINNER IN CITY			CONFERENCE BANQUET from 1830 World of Wearable Art, Nelson				

NOTE: Delegates not attending Tutorial day arrive Sunday for Registration.